

# **μΡΑ672CT**

## N-CHANNEL MOSFET FOR SWITCHING

R07DS1289EJ0200 Rev.2.00 Jul 24, 2015

### Description

The UPA672CT, N-channel vertical type MOSFET designed for general-purpose switch, is a device which can be driven directly by a 4.5 V power source.

### **Features**

- Two MOSFET circuits
- Directly driven by a 4.5 V power source.
- Low on-state resistance

 $R_{DS(on)1}$  = 2.7  $\Omega$  MAX. (Vgs = 10 V, Ip = 100 mA)

 $R_{DS(on)2} = 3.2 \Omega MAX. (V_{GS} = 4.5 V, I_{D} = 50 mA)$ 

### **Ordering Information**

Part Number	Lead Plating	Packing	Package	
UPA672CT-T1-A/AT	-A:Sn-Bi , -AT:Pure Sn	3000p/Reel	SC-88 (6pSSP)	

Remark "-AT" indicates Pb-free. This product does not contain Pb in external electrode and other parts.

### Marking UA

### **Absolute Maximum Ratings (TA = 25°C)**

Drain to Source Voltage (V <sub>GS</sub> = 0 V)	VDSS	60	V
Gate to Source Voltage (V <sub>DS</sub> = 0 V)	Vgss	±20	V
Drain Current (DC)	I <sub>D(DC)</sub>	±100	mA
Drain Current (pulse) Note	I <sub>D(pulse)</sub>	±200	mA
Total Power Dissipation	Рт	200 (Total)	mW
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

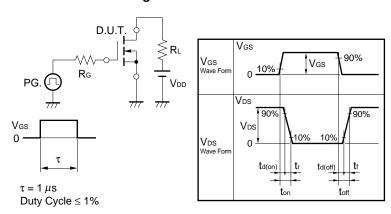
**Note** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

## Electrical Characteristics (T<sub>A</sub> = 25°C)

Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	Ipss	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	μА
Gate Leakage Current	Igss	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V			±10	μА
Gate to Source Cut-off Voltage	V <sub>GS(off)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.0		2.5	V
Forward Transfer Admittance <sup>Note</sup>	yfs	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 100 mA	150			mS
Drain to Source On-state Resistance Note	R <sub>DS(on)1</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 100 mA		2.1	2.7	Ω
	R <sub>DS(on)2</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 50 mA		2.4	3.2	Ω
Input Capacitance	Ciss	V <sub>DS</sub> = 10 V,		20		pF
Output Capacitance	Coss	V <sub>GS</sub> = 0 V,		9		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		2		pF
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10 V,		16		ns
Rise Time	<b>t</b> r	I <sub>D</sub> = 200 mA,		6.5		ns
Turn-off Delay Time	t <sub>d(off)</sub>	V <sub>GS</sub> = 10 V,		82		ns
Fall Time	tf	R <sub>G</sub> = 10 Ω		32		ns
Total Gate Charge	Q <sub>G</sub>	I <sub>D</sub> = 200 mA, V <sub>DD</sub> = 25 V, V <sub>GS</sub> = 10 V		2		nC
Body Diode Forward Voltage Note	V <sub>F(S-D)</sub>	I <sub>F</sub> = 200 mA, V <sub>GS</sub> = 0 V		0.86		V

Note Pulsed

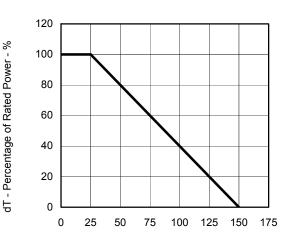
## **Test Circuit Switching Time**



Ib - Drain Current - mA

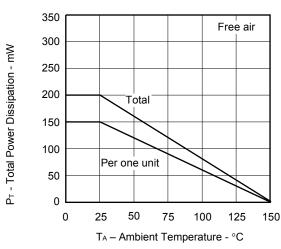
### Typical Characteristics (T<sub>A</sub> = 25°C)

## DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



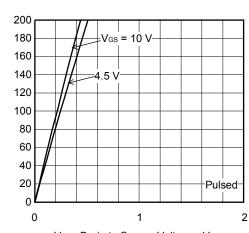
T<sub>A</sub> – Ambient Temperature - °C

TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



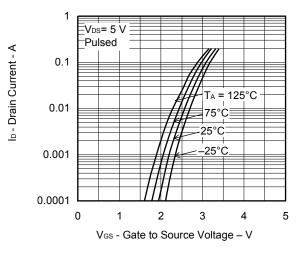
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DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

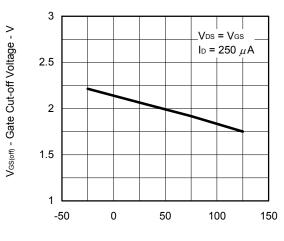


 $V_{\text{\scriptsize DS}}$  - Drain to Source Voltage - V

FORWARD TRANSFER CHARACTERISTICS

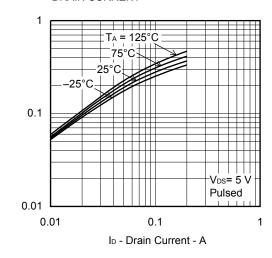


GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



 $T_{\text{ch}}$  - Channel Temperature -  $^{\circ}C$ 

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



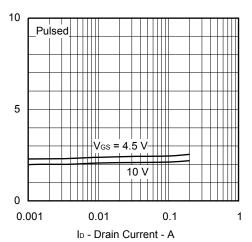
| yfs | - Forward Transfer Admittance -

 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$  - Drain to Source On-state Resistance -  $\Omega$ 

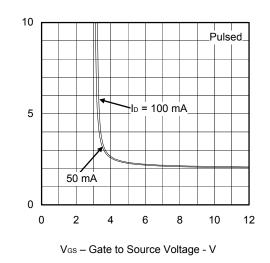
 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$  - Drain to Source On-state Resistance -  $\Omega$ 

ta(on), tr, ta(off), tr - Switching Time - ns

DRAIN TO SOURCE ON-STATE RESISTANCE vs. **DRAIN CURRENT** 

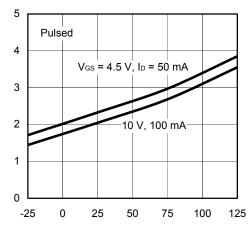


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

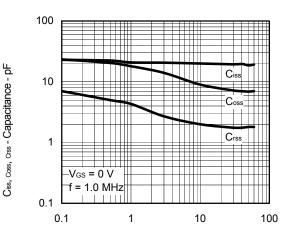


 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$  - Drain to Source On-state Resistance -  $\Omega$ 

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



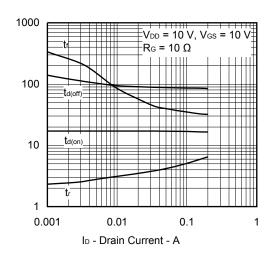
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



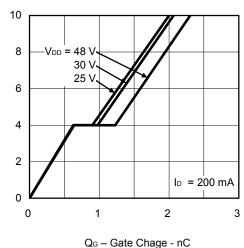
Tch - Channel Temperature - °C

 $V_{\text{\scriptsize DS}}$  - Drain to Source Voltage – V

### SWITCHING CHARACTERISTICS

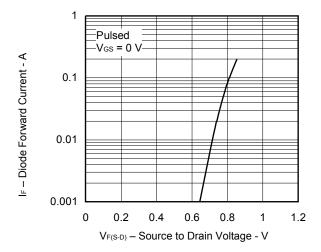


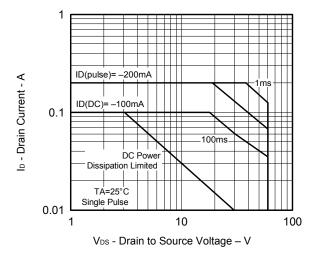
## DYNAMIC INPUT CHARACTERISTICS



Ves - Gate to Source Voltage - V

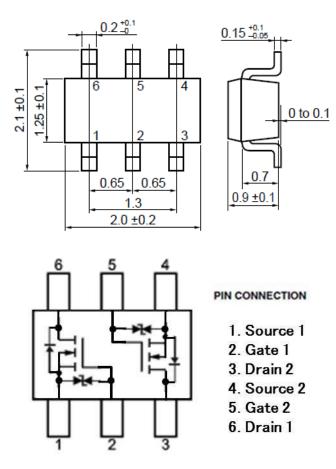
### FORWARD BIAS SAFE OPERATING AREA



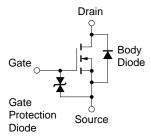


### Package Drawings (Unit: mm)

### SC-88 (6pSSP)



### **Equivalent Circuit**



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

## μΡΑ672СΤ

		Description		
Rev.	Date	Page	Summary	
1.00	Sep , 2013	_	First Edition Issued	
2.00	Jul, 2015	2	- Changed Electrical Characteristics	
			- Changed Test Circuit Switching Time	
		3, 4, 5	Changed all graphs	

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